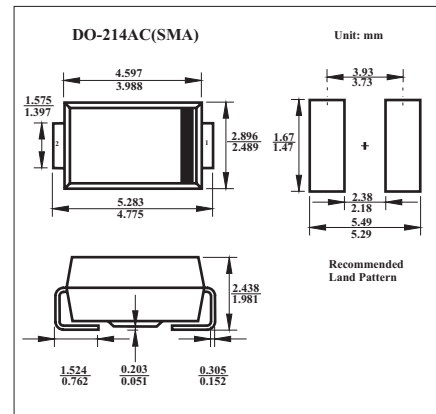


Schottky Barrier Rectifier Diodes KL12 THRU KL14

■ Features

- For Surface Mounted Applications
- Metal Silicon Junction, Majority Carrier Conduction
- Low Power Loss, High Efficiency
- High Forward Surge Current Capability



■ Maximum Ratings and Electrical Characteristics @ Ta = 25°C

Parameter	Symbol	KL12	KL13	KL14	Unit
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	20	30	40	V
Maximum RMS voltage	V _{RMS}	14	21	28	
Maximum DC Blocking Voltage	V _{DC}	20	30	40	
Maximum Average Forward Rectified Current	I(AV)	1.0			A
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	30			A
Maximum Instantaneous Forward Voltage at 1.0A	V _F	0.38	0.38	0.40	V
Maximum DC Reverse Current TA=25°C	I _R	0.5			mA
At Rated DC Blocking Voltage TA=100°C		20			
Typical Thermal Resistance *	R _{θJA}	88.0			°C/W
	R _{θJL}	28			
Operating Junction Temperature Range	T _J	-55 to +125			°C
Storage Temperature Range	T _{STG}	-55 to +150			°C

* P.C.B mounted with 0.2X0.2"(5.0x5.0mm)copper pad areas